

Abstract of the Disclosure

On a substrate 1 is formed a first transparent electrode layer 3, on which a p-type semiconductor film 5, an i-type semiconductor film 6 and an n-type semiconductor film 7 are successively formed to constitute an electric power generating layer. On the n-type semiconductor film 7 is formed a second transparent electrode layer 8, on which a back electrode layer 9 is formed. Moreover, an intermediate layer 4 made of a given material is formed between the first transparent electrode layer 3 and the p-type semiconductor film 5 to complete a photovoltaic element 40 with high electric power generating efficiency (conversion efficiency).